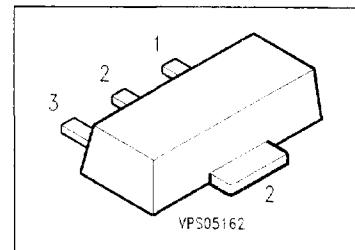


Silicon Switching Diodes

BAW 78 A
... **BAW 78 D**

- Switching applications
- High breakdown voltage



| Type | Marking | Ordering Code (tape and reel) | Pin Configuration | Package ¹⁾ |
|----------|---------|----------------------------------|---------------------|-----------------------|
| BAW 78 A | GA | Q62702-A778 | | |
| BAW 78 B | GB | Q62702-A779 | | |
| BAW 78 C | GC | Q62702-A784 | | |
| BAW 78 D | GD | Q62702-A109 | EIA07007 | SOT-89 |

Maximum Ratings

| Parameter | Symbol | Values | | | | Unit |
|--|-----------|----------|----------|----------------|----------|------------|
| | | BAW 78 A | BAW 78 B | BAW 78 C | BAW 78 D | |
| Reverse voltage | V_R | 50 | 100 | 200 | 400 | V |
| Peak reverse voltage | V_{RM} | 50 | 100 | 200 | 400 | |
| Forward current | I_F | | | 1 | | A |
| Peak forward current | I_{FM} | | | 1 | | |
| Surge forward current $t = 1 \mu s$ | I_{FS} | | | 10 | | |
| Total power dissipation $T_s = 125^\circ C$ | P_{tot} | | | 1 | | W |
| Junction temperature | T_j | | | 150 | | $^\circ C$ |
| Storage temperature range | T_{stg} | | | - 65 ... + 150 | | |

Thermal Resistance

| | | | |
|----------------------------------|------------|-----------|-----|
| Junction - ambient ²⁾ | R_{thJA} | ≤ 95 | K/W |
| Junction - soldering point | R_{thJS} | ≤ 25 | |

¹⁾ For detailed information see chapter Package Outlines.

²⁾ Package mounted on epoxy pcb 40 mm x 40 mm x 1.5 mm/6 cm² Cu.

Electrical Characteristicsat $T_A = 25^\circ\text{C}$, unless otherwise specified.

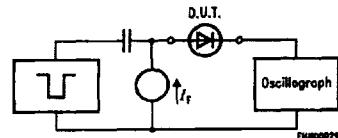
| Parameter | Symbol | Values | | | Unit |
|-----------|--------|--------|------|------|------|
| | | min. | typ. | max. | |

DC characteristics

| | | | | | |
|--|------------|---|---|----------|---------------|
| Breakdown voltage $I_{(BR)} = 100 \mu\text{A}$ | $V_{(BR)}$ | | | | V |
| BAW 78 A | 50 | — | — | — | |
| BAW 78 B | 100 | — | — | — | |
| BAW 78 C | 200 | — | — | — | |
| BAW 78 D | 400 | — | — | — | |
| Forward voltage ¹⁾ $I_F = 1 \text{ A}$ $I_F = 2 \text{ A}$ | V_F | | | 1.6 2 | V |
| Reverse current $V_R = V_{R\text{max}}$ $V_R = V_{R\text{max}}, T_A = 150^\circ\text{C}$ | I_R | — | — | 1 50 | μA |

AC characteristics

| | | | | | |
|---|----------|---|----|---|---------------|
| Diode capacitance $V_R = 0, f = 1 \text{ MHz}$ | C_D | — | 10 | — | pF |
| Reverse recovery time $I_F = 200 \text{ mA}, I_R = 200 \text{ mA},$ $R_L = 100 \Omega$ measured at $I_R = 20 \text{ mA}$ | t_{rr} | — | 1 | — | μs |

Test circuit for reverse recovery time

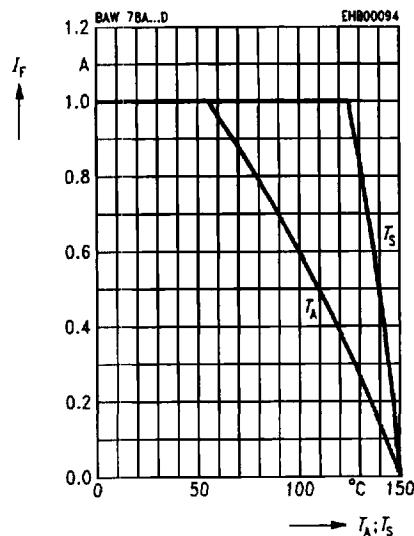
Pulse generator: $t_p = 5 \mu\text{s}$, $D = 0.05$
 $t_r = 0.6 \text{ ns}$, $R_i = 50 \Omega$

Oscilloscope: $R = 50 \Omega$
 $t_r = 0.35 \text{ ns}$
 $C \leq 1 \text{ pF}$

¹⁾ Pulse test: $t_p \leq 300 \mu\text{s}$, $D = 2 \%$.

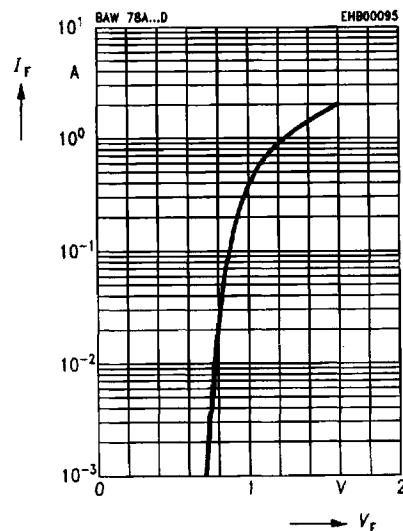
Forward current $I_F = f(T_A^*, T_S)$

* Package mounted on epoxy



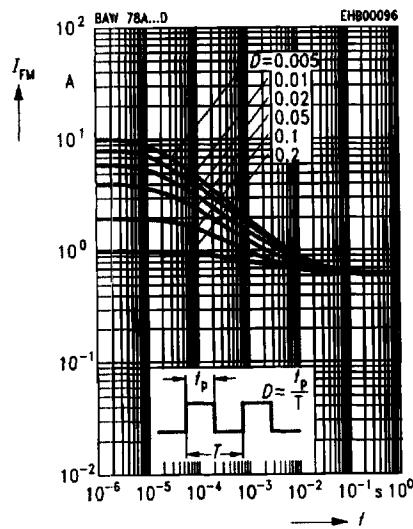
Forward current $I_F = f(V_F)$

$T_A = 25^\circ\text{C}$



Peak forward current $I_{FM} = f(t)$

$T_A = 25^\circ\text{C}$



Reverse current $I_R = f(T_A)$

$V_R = V_{Rmax}$

